TOSHIBA Transistor Silicon NPN Epitaxial Planar Type (PCT process)

2SC2714

High Frequency Amplifier Applications FM, RF, MIX,IF Amplifier Applications

- Small reverse transfer capacitance: $C_{re} = 0.7 pF$ (typ.)
- Low noise figure: NF = 2.5dB (typ.) (f = 100 MHz)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V _{CEO}	30	٧
Emitter-base voltage	V _{EBO}	4	V
Collector current	IC	20	mA
Base current	Ι _Β	4	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Unit: mm

1. BASE
2. EMITTER
3. COLLECTOR

JEDEC

JEITA

SC-59

TOSHIBA

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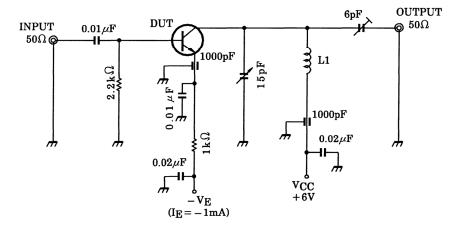
Weight: 0.012 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 18 V, I _E = 0	_	_	0.5	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = 4 \text{ V}, I_{C} = 0$	_	_	0.5	μΑ
DC current gain	h _{FE} (Note)	V _{CE} = 6 V, I _C = 1 mA	40	_	200	
Reverse transfer capacitance	C _{re}	V _{CB} = 6 V, f = 1 MHz	_	0.70	_	pF
Transition frequency	f _T	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$	_	550	_	MHz
Collector-base time constant	C _c .rbb'	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 30 \text{ MHz}$	_	_	30	ps
Noise figure	NF	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 100 \text{ MHz},$	_	2.5	5.0	dB
Power gain	G _{pe}	Figure 1	17	23	_	dB

Note: hFE classification R: 40~80, O: 70~140, Y: 100~200



L1: 0.8 mm ϕ silver plated copper wire, 4 T, 10ID, 8 length

Figure 1 NF, Gpe Test Circuit

y Parameter (typ.)

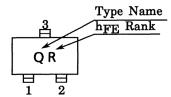
(1) Common emitter (VCE = 6 V, IE = -1 mA, f = 100 MHz)

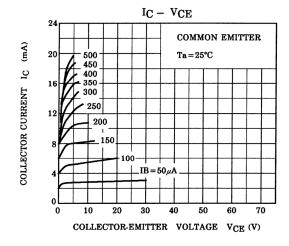
Characteristics	Symbol	Тур.	Unit
Input conductance	gie	2.9	mS
Input capacitance	C _{ie}	10.2	pF
Reverse transfer admittance	y _{re}	0.33	mS
Phase angle of reverse transfer admittance	$\theta_{\sf re}$	-90	٥
Forward transfer admittance	lу _{fe} l	40	mS
Phase angle of forward transfer admittance	$\theta_{\sf fe}$	-20	0
Output conductance	9 _{oe}	45	μS
Output capacitance	C _{oe}	1.1	pF

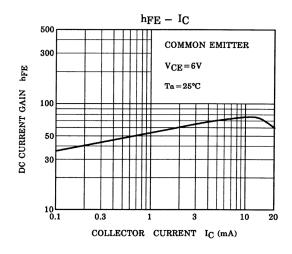
(2) Common base ($V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}, f = 100 \text{ MHz}$)

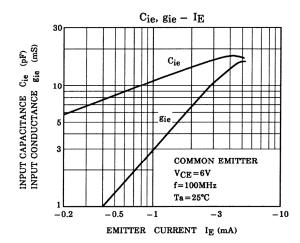
(2) Common base (VCE = 0 V, TE = 1 mr, 1 = 100 MHz)				
Characteristics	Symbol	Тур.	Unit	
Input conductance	9ib	34	mS	
Input capacitance	C _{ib}	-10	pF	
Reverse transfer admittance	y _{rb}	0.27	mS	
Phase angle of reverse transfer admittance	$\theta_{\sf rb}$	-105	٥	
Forward transfer admittance	ly _{fb} l	34	mS	
Phase angle of forward transfer admittance	θ_{fb}	165	٥	
Output conductance	gob	45	μS	
Output capacitance	C _{ob}	1.1	pF	

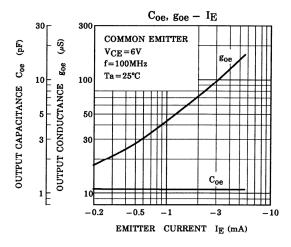
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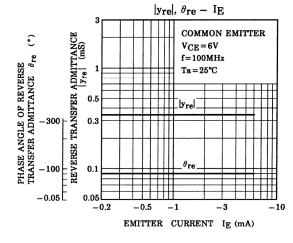


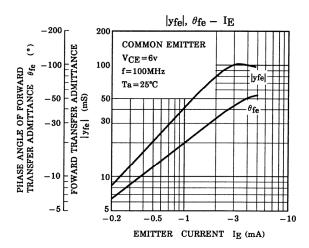


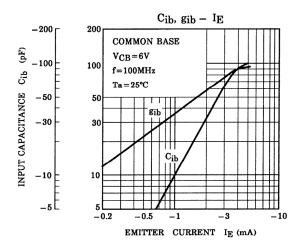


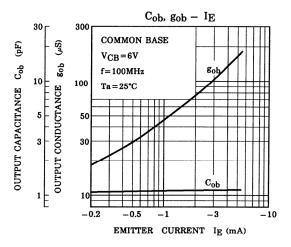


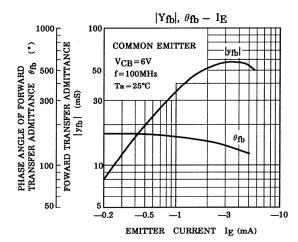


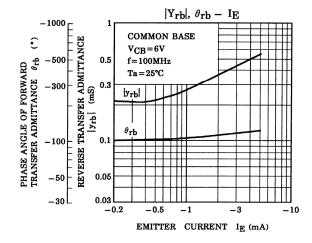


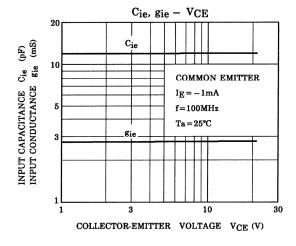


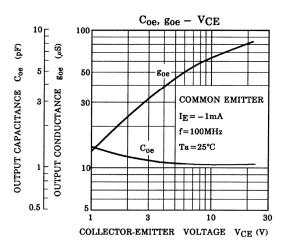


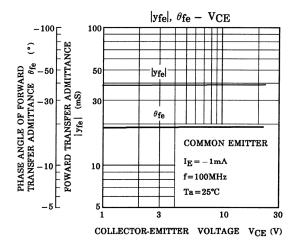


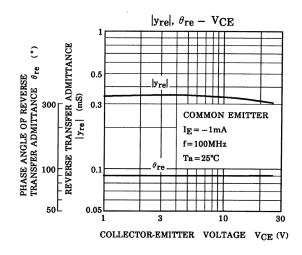


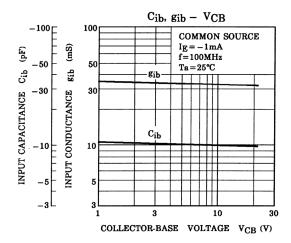


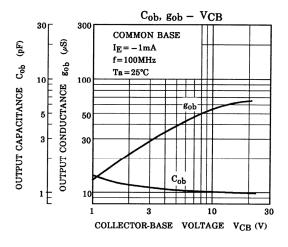


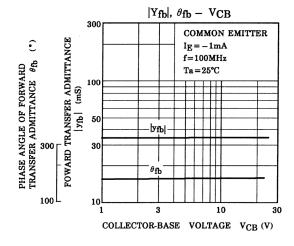


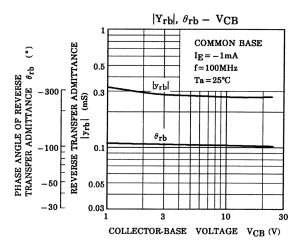


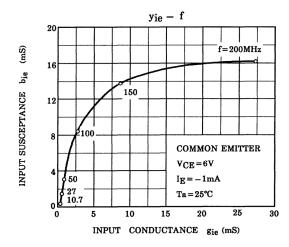


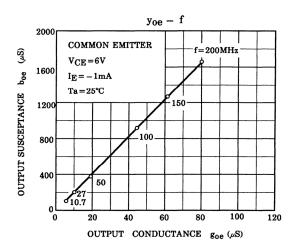


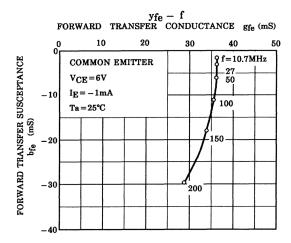


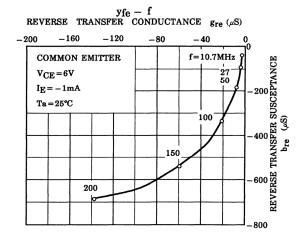


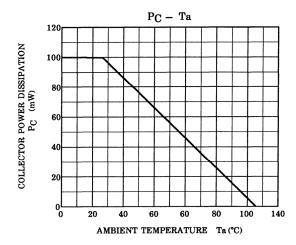












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20070701-EN GENERAL

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